

Serial No. 10/070,554

B1
conc. wiring line has a five-layered structure composed of a gate wiring line metal film, a gate insulating film, a semiconductor film, a contact metal film layer, and a metal electrode film.

Page 29, line 16, to Page 30, line 10, cancel and replace with:

Ba There is provided a method of fabricating a liquid crystal display device comprising: fabricating a first bottom-gate TFT array substrate including forming at least a gate wiring line metal film, a gate insulating film, a semiconductor film, and a contact metal film layer on a surface of an insulating substrate; by photolithography, sequentially etching the contact metal film layer, the semiconductor film, the gate insulating film, and the gate wiring line metal film, using a first pattern; oxidizing side surfaces of portions of a metal film pattern to be formed into gate wiring lines and gate electrodes; forming a metal electrode film; by photolithography, sequentially etching part of the metal electrode film, the contact metal film layer, and the semiconductor film, using a second pattern; and forming second comb-shaped pixel electrodes, using a third pattern, with a passivation film disposed between the second comb-shaped pixel electrodes and the substrate;

Serial No. 10/070,554

B2
conc.

forming an alignment film on the first substrate; forming an alignment film on a surface of a color filter side of a second color filter substrate; adhering and fixing the first and second substrates at the periphery thereof such that the substrates are arranged with the two alignment films facing inside and with a predetermined gap maintained between the substrates; and injecting a specified liquid crystal between the first and second substrates.

Page 51, line 23, to Page 52, line 5, cancel and replace with:

B3

Subsequently, a second resist pattern for the second photolithography was formed by a conventional method. Then, part of the metal electrode film, the contact electrode metal, and the n+a-Si film on the gate electrode were sequentially etched away through to the i-type a-Si film, thus forming channel regions. The source segmented wiring line was connected to a source region by a portion of the contact electrode metal and a metal electrode, and a second comb-shaped pixel metal electrode was connected to a drain region by a portion of the contact electrode metal.

Page 52, lines 6 to 9, cancel and replace with:

B4 At this point, the source segmented wiring lines, which had been previously severed, were connected together on the gate wiring line by the metal electrode film pattern via a portion of the contact electrode metal.

Page 54, lines 7 to 15, cancel and replace with:

B5 First, there were provided a TFT array substrate for the IPS mode device, similar to that of Example 2-5, fabricated using two masks, more specifically, a first TFT array substrate including a first comb-shaped electrode group and a second comb-shaped electrode group arranged in a matrix and a transistor group that drives the second comb-shaped electrode group; and a color filter substrate including a second color filter substrate group placed opposite to the first and second electrode groups. Over each of the substrates, by a conventional method, a polyimide resin was applied and cured, and the resulting films were subjected to rubbing, thus producing liquid crystal alignment films.

Page 56, line 25, to Page 57, line 8, cancel and replace with:

B6 Subsequently, a second resist pattern for the second

Serial No. 10/070,554

B6
Conc.

photolithography, which includes second comb-shaped pixel metal electrodes, was formed by a conventional method. Then, part of the metal electrode film, the contact metal film layer (Ti), and the n+a-Si film on the gate electrode were sequentially etched away, thus forming channel regions. The source segmented wiring line was connected to a source region by a portion of a contact metal film layer (Ti) and a metal electrode film pattern, and a second comb-shaped pixel metal electrode 262 was connected to a drain region by a portion of the contact electrode metal.

Page 58, line 18, to Page 59, line 1, cancel and replace with:

B7

First, there were provided a TFT array substrate for the IPS mode device, similar to that of Example 2-7, fabricated using two masks, more specifically, a first TFT array substrate including a first comb-shaped electrode group and a second comb-shaped electrode group arranged in a matrix and a transistor group that drives the second comb-shaped electrode group; and a second color filter substrate including a color filter group placed opposite to the first and second electrode groups. Over each of the substrates, by a conventional method, a polyimide resin was applied

Serial No. 10/070,554

B7
conc. and cured, and the resulting films were subjected to rubbing, thus producing liquid crystal alignment films.

Page 61, lines 10 to 14, cancel and replace with:

B8 At this point, the source segmented wiring lines, which had been previously severed, were connected together on the gate wiring line by the metal electrode via a portion of the contact electrode metal.

Page 62, lines 15 to 20, cancel and replace with:

B9 Furthermore, when part of the source segmented wiring line had a five-layered structure composed of the gate wiring line metal film, the gate insulating film, the semiconductor film, the contact metal film layer, and the metal electrode film, it was possible to reduce the resistance of the source segmented wiring line, allowing fabrication of a TFT array substrate having few variations in characteristics.

Page 63, line 23, to Page 64, line 5, cancel and replace with:

B10

Next, the first and second substrates were arranged such that their respective alignment films oppose one another, thus producing a cell having a gap of about 5 microns, which is created by spacers and adhesives. Thereafter, a TN liquid crystal was injected between the first and second substrates, and polarizers were then arranged so as to have a crossed Nicols relation, thus completing a display device.

Page 66, lines 5 to 9, [✓]cancel and [✓]replace with:

B11

At this point, the source segmented wiring lines, which had been previously severed, were connected together on the gate wiring line by the two-layered structure composed of the metal electrode and a portion of the contact electrode metal.

Page 67, lines 15 to 21, cancel and replace with:

B12

Next, the first and second substrates were arranged such that their respective alignment films oppose one another, thus producing a cell having a gap of about 5 microns, which is created by spacers and adhesives. Thereafter, a TN liquid crystal was injected between the first and second substrates, and polarizers were then

Serial No. 10/070,554

B12
conc.

arranged so as to have a crossed Nicols relation, thus completing a display device.
